

MergeOptics GmbH
M60066PCT

Abstract of the Disclosure

A method of manufacturing a heterobipolar transistor

The invention relates to a method of manufacturing a heterobipolar transistor, wherein epitaxially grown layers (2 to 11) on a
5 substrate (1) are structured by etching. An emitter contact (31) and a base contact (32) are formed by simultaneous metallizing of an emitter layer (11) and a base layer (6). This method reduces the number of method steps required to manufacture a heterobipolar transistor and thus cuts time and cost which must be invested in
10 production.

(Fig. 7)